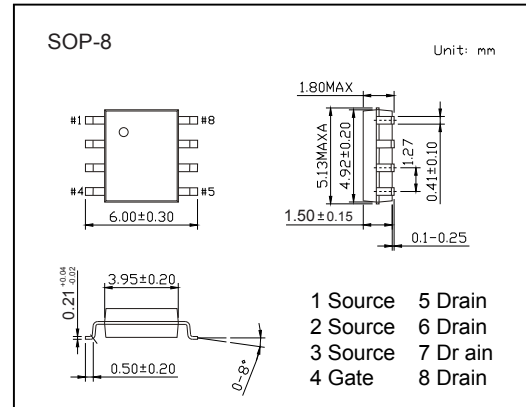


P-Channel MOSFET

KX5P02

■ Features

- $V_{DS} (V) = -20V$
- $I_D = -5 A$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 50m\Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 85m\Omega$ ($V_{GS} = -4.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	
Continuous Drain Current	I_D	-5	A
Power Dissipation	P_D	2	W
Thermal Resistance Junction- to-Ambient	R_{thJA}	62.5	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -250 \mu A, V_{GS} = 0V$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -18V, V_{GS} = 0V$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 10V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4		-0.9	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -5A$			50	m Ω
		$V_{GS} = -4.5V, I_D = -4A$			85	
Forward Transconductance	g_{FS}	$V_{DS} = -5V, I_D = -5A$	4			S
Maximum Body-Diode Continuous Current	I_S				-1.3	A
Diode Forward Voltage	V_{SD}	$I_S = -1.3A, V_{GS} = 0V$			-1.1	V

■ Marking

Marking	5P02 K***
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